

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	113	(common near etch\$3) near (process)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
2	BRS	L2	11	(common near etch\$3) near (openings)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
3	BRS	L3	59	(common near5 etch\$3) near (openings)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
4	BRS	L4	0	(common near5 etch\$3) near (openings) near15 (time)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
5	BRS	L5	1	(common near5 etch\$3) near (openings) same (time)	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B
6	BRS	L6	48	(common near5 etch\$3) near (openings) and (time)	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B
7	BRS	L7	13442	((actual) near3 (dimension or diameter))	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B
8	BRS	L8	11374	((actual) near2 (dimension or diameter))	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B

	Type	L #	Hits	Search Text	DBs
9	BRS	L10	3	((actual) near2 (dimension or diameter)) near15 (openings) near15 (time)	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B
10	BRS	L9	142	((actual) near2 (dimension or diameter)) near15 (openings)	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B
11	BRS	L11	165941	438?\$.ccls.	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B
12	BRS	L12	165941	"438"/\$.ccls.	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B

	Type	L #	Hits	Search Text	DBs
13	BRS	L13	14	9 and 12	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	U	1	Document ID	Title
1			US 20040222486 A1	BiCMOS TECHNOLOGY ON SOI SUBSTRATES
2			US 20040203198 A1	MOSFET device with nanoscale channel and method of manufacturing the same
3			US 20010001497 A1	Semiconductor device and method for manufacturing the same
4			US 6207996 B1	Semiconductor device and method for manufacturing the same
5			US 5521399 A	Advanced silicon on oxide semiconductor device structure for BiCMOS integrated circuit
6			US 5484738 A	Method of forming silicon on oxide semiconductor device structure for BiCMOS integrated circuits

	U	1	Document ID	Title
7			JP 11087723 A	FABRICATION OF SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE
8			US 20040203198 A	Manufacture of metal oxide semiconductor field effect transistor device, comprises forming first silicon oxide film pattern doped with first impurity, and forming second silicon oxide film spacer doped with second impurity
9	X		EP 575283 A	BICMOS bonded silicon on oxide semiconductor device structure - by simultaneous formation of deep and shallow regions and without need for high temp. epitaxial processing